

ABSTRACT OF THE DISCLOSURE

At present, Cu (copper) is being used as a wiring material. In an RF-CMOS device as a combination of an RF analog device and CMOS logic device, two electrodes
5 of a MIM capacitor are formed from Cu having a large diffusion coefficient. To prevent Cu from diffusing to the capacitor insulating film of the MIM capacitor, diffusion prevention films having a function of preventing diffusion of Cu are interposed between the
10 capacitor insulating film and the two electrodes. As a result, Cu forming the electrodes does not diffuse to the capacitor insulating film.